

**Patent number:** JP2000183451  
**Publication date:** 2000-06-30  
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**Classification:**  
**- international:** H01S5/10; H01S5/34  
**- european:**  
**Application number:** JP19980356330 19981215  
**Priority number(s):**

**PROBLEM TO BE SOLVED:** To provide a nitride system semiconductor laser element, where a resonator surface that is vertical to the surface of a substrate, can be easily formed and yield is improved, and to provide its manufacturing method.

**SOLUTION:** A step part 100 with a side surface 101 and a bottom surface 102 in parallel with the direction  $\langle 11\text{-}20 \rangle$  of a sapphire substrate 1 is formed on a surface (0001) of the sapphire substrate 1. A GaN(gallium nitride) based semiconductor layer 15 containing an MQW(multiple quantum well) luminous layer 7 is subjected to the epitaxial growth on the upper surface of the sapphire substrate 1 and the side surface 101 and the bottom surface 102 of the step part 100. During the crystal growth of the GaN system semiconductor layer 15, a surface  $11\text{-}20$  that is completely vertical with respect to the surface (0001) of the sapphire substrate 1 is formed on the side surface 101 of the step part 100. The surface  $11\text{-}20$  of the GaN system semiconductor layer 15 on the side surface 101 of the step part 100 is used as a resonator surface 200.

